



STB30NM60N, STI30NM60N, STF30NM60N STP30NM60N, STW30NM60N

N-channel 600 V, 0.1 Ω , 25 A, MDmesh™ II Power MOSFET
TO-220, TO-220FP, TO-247, D²PAK, I²PAK

Features

Type	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D	P _W
STB30NM60N	650 V	<0.13 Ω	25A	190 W
STI30NM60N	650 V	<0.13 Ω	25A	190 W
STF30NM60N	650 V	<0.13 Ω	25A ⁽¹⁾	40 W
STP30NM60N	650 V	<0.13 Ω	25A	190 W
STW30NM60N	650 V	<0.13 Ω	25A	190 W

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices is designed using the second generation of MDmesh™ Technology. This revolutionary Power MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

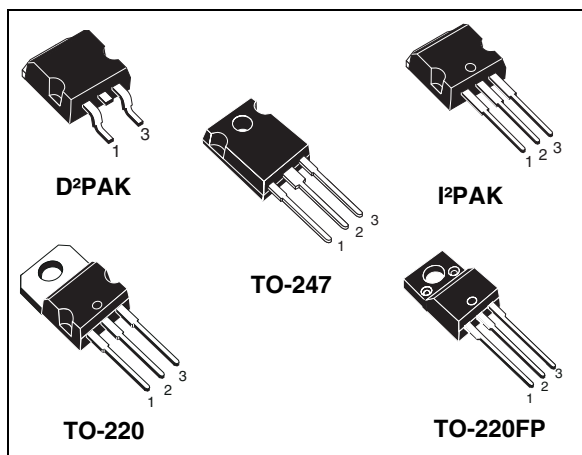


Figure 1. Internal schematic diagram

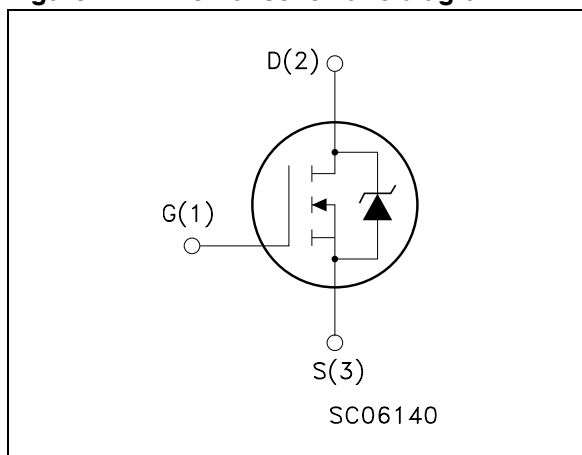


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB30NM60N	30NM60N	D ² PAK	Tape and reel
STI30NM60N	30NM60N	I ² PAK	Tube
STF30NM60N	30NM60N	TO-220FP	Tube
STP30NM60N	30NM60N	TO-220	Tube
STW30NM60N	30NM60N	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value					Unit
		TO-220	I ² PAK	TO-247	D ² PAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} =0)	600					V
V _{GS}	Gate-source voltage	± 30					V
I _D	Drain current (continuous) at T _C = 25 °C	25			25 ⁽¹⁾		A
I _D	Drain current (continuous) at T _C = 100 °C	15.8			15.8 ⁽¹⁾		A
I _{DM} ⁽²⁾	Drain current (pulsed)	100			100 ⁽¹⁾		A
P _{TOT}	Total dissipation at T _C = 25 °C	190			40		W
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15					V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T _C =25 °C)	--			2500		V
T _{stg}	Storage temperature	-55 to 150					°C
T _j	Max. operating junction temperature	150					°C

1. Limited only by maximum temperature allowed

2. Pulse width limited by safe operating area

3. I_{SD} ≤ 25A, di/dt ≤ 400A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	TO-220	I ² PAK	TO-247	D ² PAK	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case max	0.66				3.1	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max	--	--	--	30	--	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5		50	--	62.5	°C/W
T _l	Maximum lead temperature for soldering purposes	300					°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	12	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25°C, I _D = I _{AR} , V _{DD} = 50V)	900	mJ

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125^\circ\text{C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$, $I_D = 12.5 \text{ A}$		0.1	0.13	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}$, $I_D = 12.5 \text{ A}$		25		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$		2700 210 22		pF pF pF
$C_{oss \text{ eq.}}$	Equivalent Output capacitance	$V_{GS} = 0$, $V_{DS} = 0 \text{ to } 480 \text{ V}$		66		pF
R_g	Gate input resistance	$f = 1 \text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain		3		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}$, $I_D = 25 \text{ A}$, $V_{GS} = 10 \text{ V}$ (see Figure 19)		91 14 50		nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N Electrical characteristics
Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 12.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18)		20		ns
t_r	Rise time			24		ns
$t_{d(off)}$	Turn-off-delay time			125		ns
t_f	Fall time			70		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				25	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				100	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 25\text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 23)		540		ns
Q_{rr}	Reverse recovery charge			10		μC
I_{RRM}	Reverse recovery current			36		A
t_{rr}	Reverse recovery time	$I_{SD} = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150^\circ\text{C}$ (see Figure 23)		630		ns
Q_{rr}	Reverse recovery charge			12		μC
I_{RRM}	Reverse recovery current			36		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / D²PAK / I²PAK

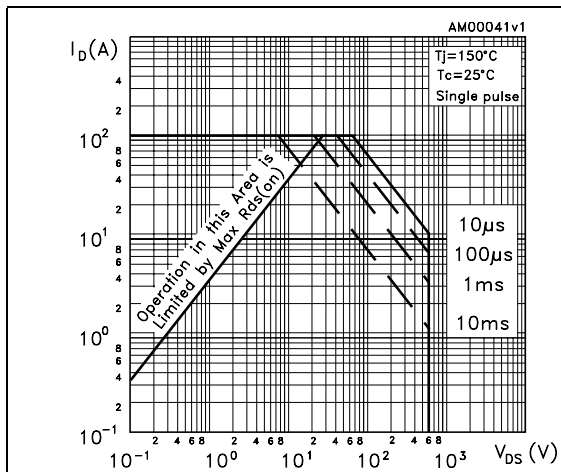


Figure 3. Thermal impedance for TO-220 / D²PAK / I²PAK

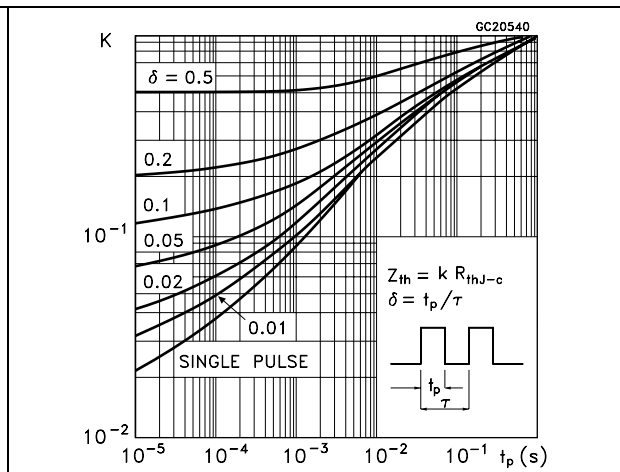


Figure 4. Safe operating area for TO-220FP

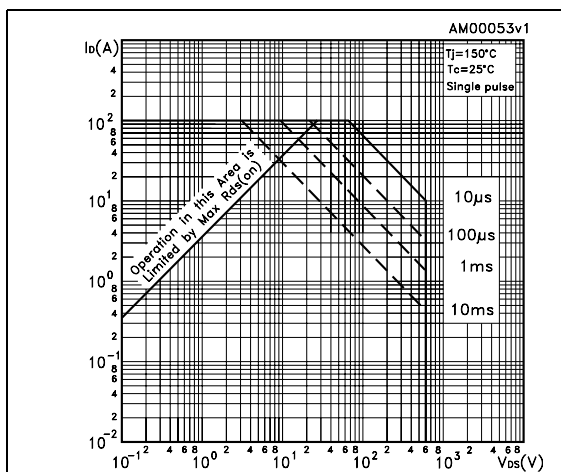


Figure 5. Thermal impedance for TO-220FP

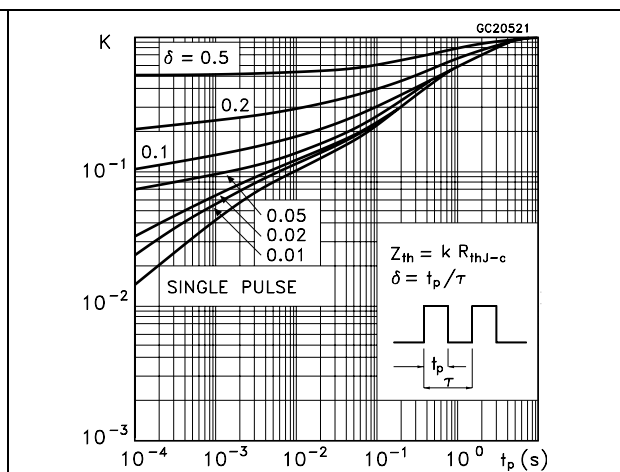


Figure 6. Safe operating area for TO-247

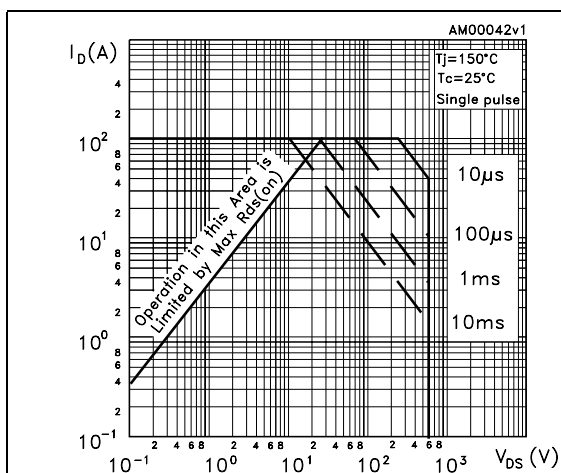
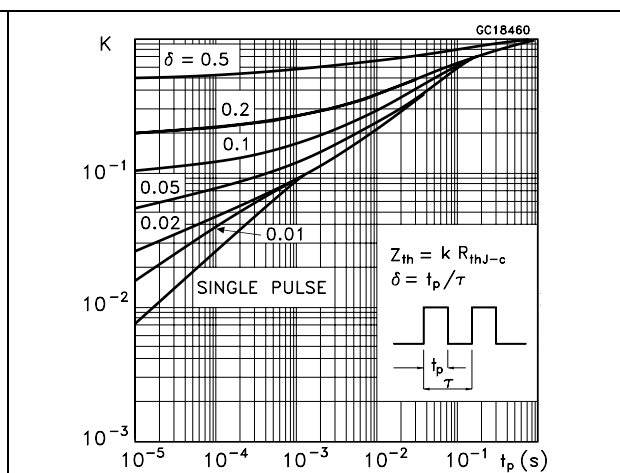
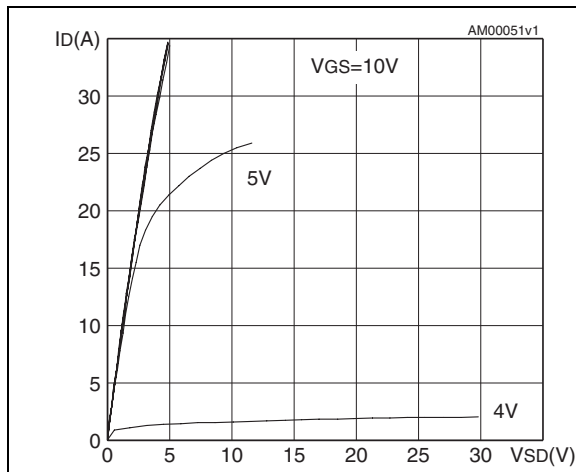
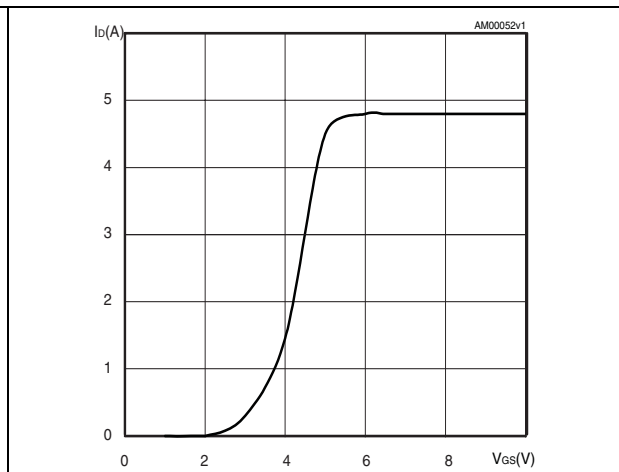
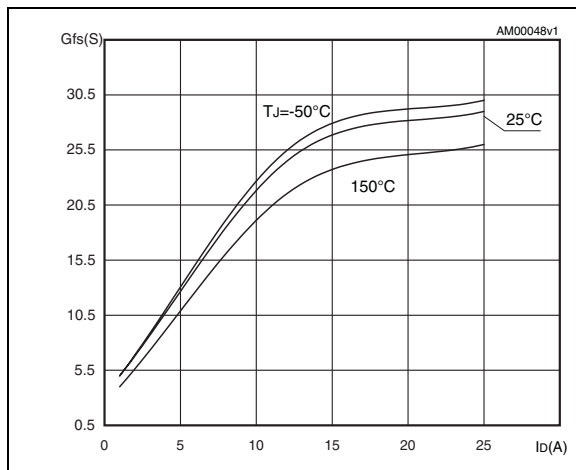
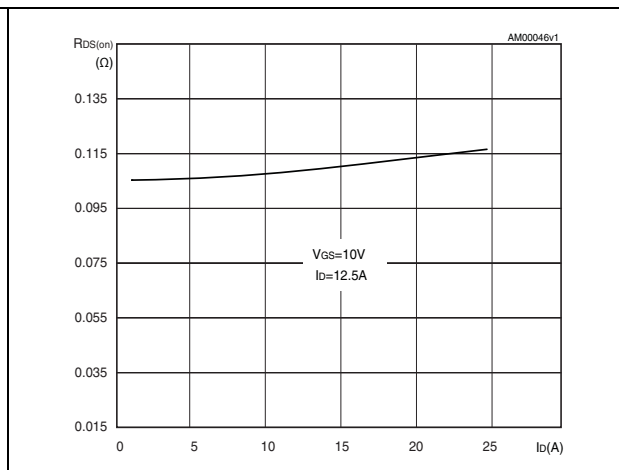
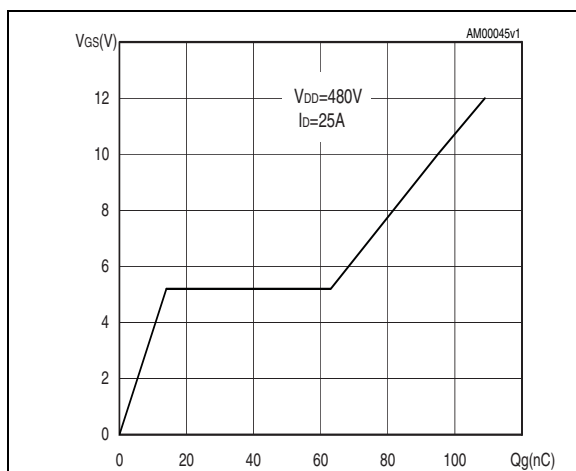
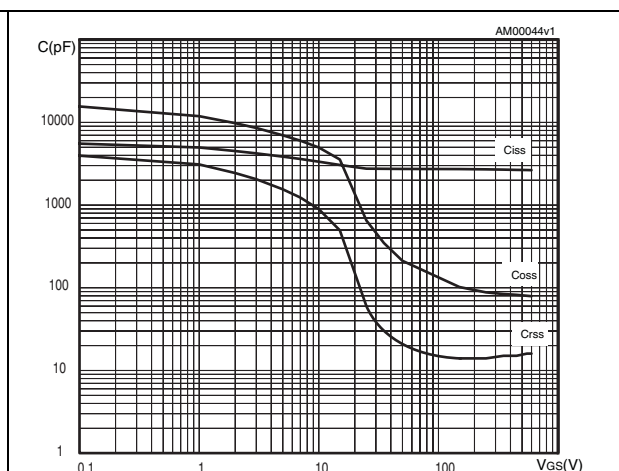


Figure 7. Thermal impedance for TO-247



STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N Electrical characteristics
Figure 8. Output characteristics

Figure 9. Transfer characteristics

Figure 10. Transconductance

Figure 11. Static drain-source on resistance

Figure 12. Gate charge vs gate-source voltage

Figure 13. Capacitance variations


Electrical characteristics STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N

Figure 14. Normalized gate threshold voltage vs temperature

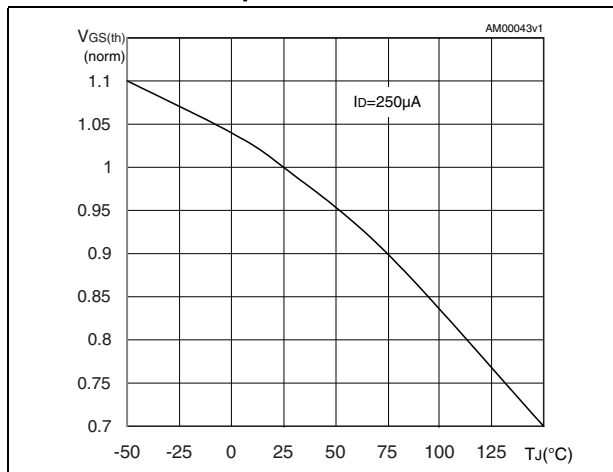


Figure 15. Normalized on resistance vs temperature

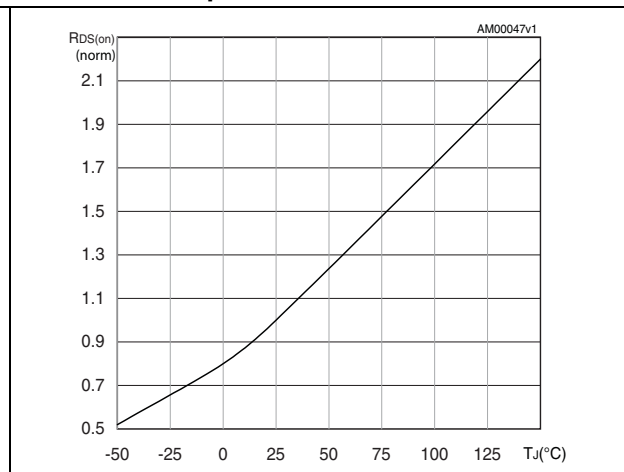


Figure 16. Source-drain diode forward characteristics

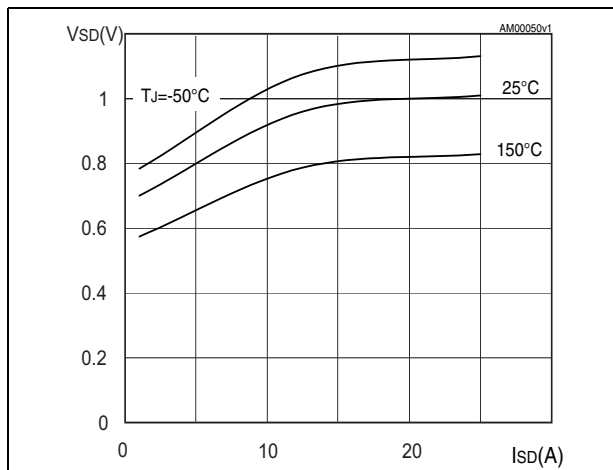
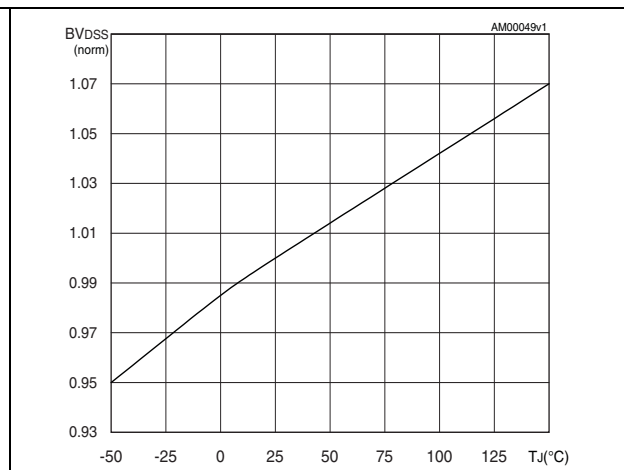


Figure 17. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

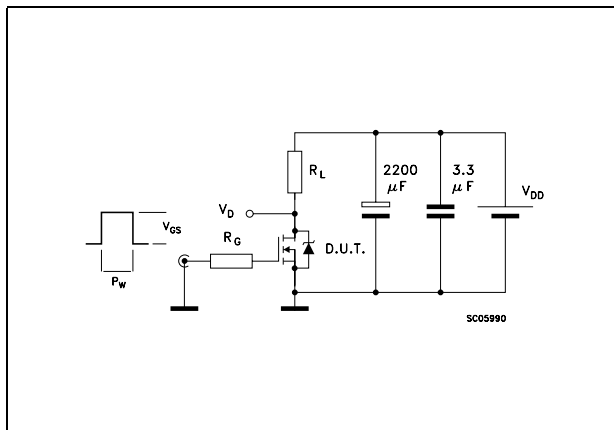


Figure 19. Gate charge test circuit

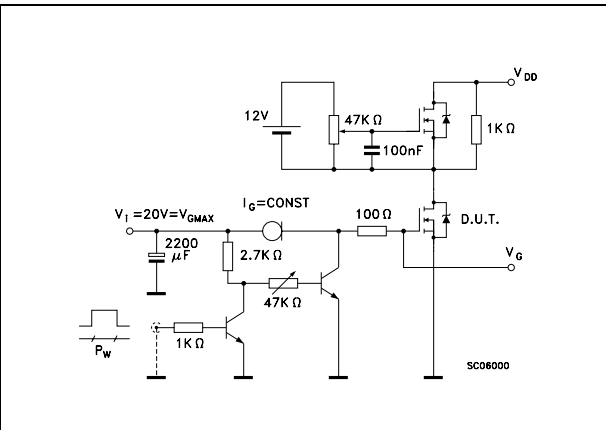


Figure 20. Test circuit for inductive load switching and diode recovery times

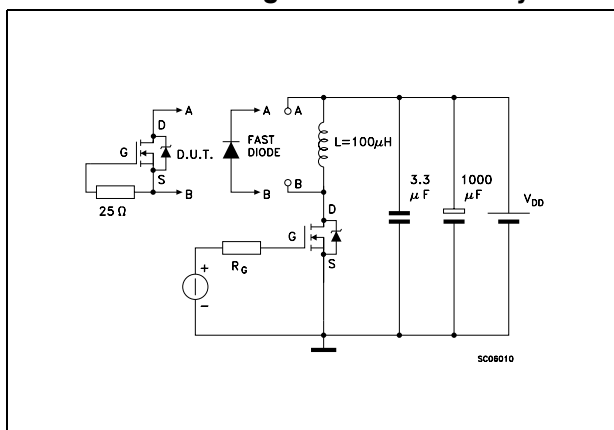


Figure 21. Unclamped inductive load test circuit

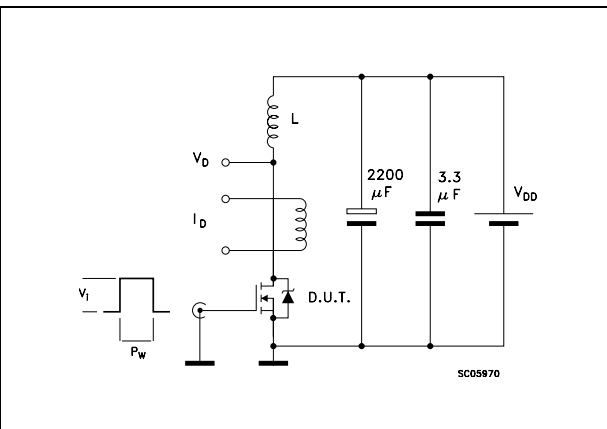


Figure 22. Unclamped inductive waveform

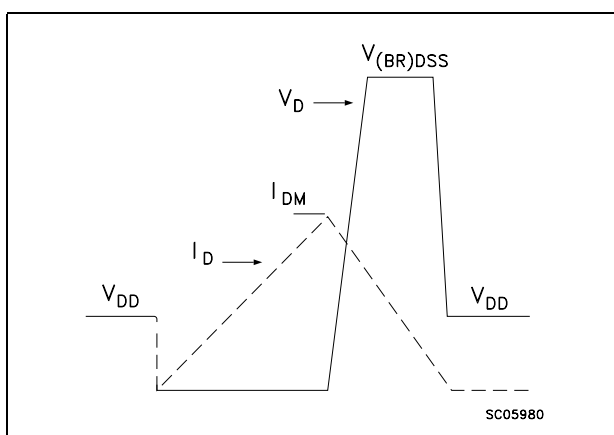
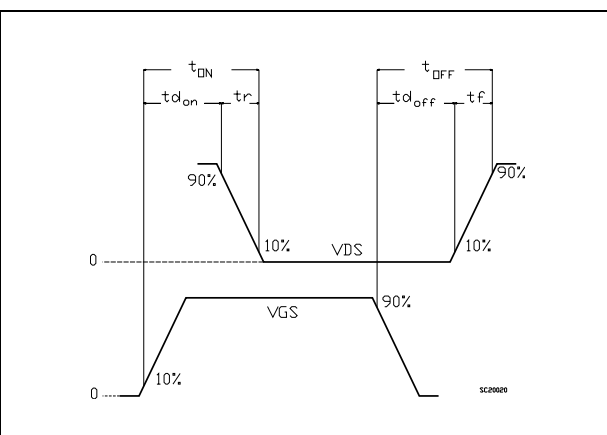


Figure 23. Switching time waveform

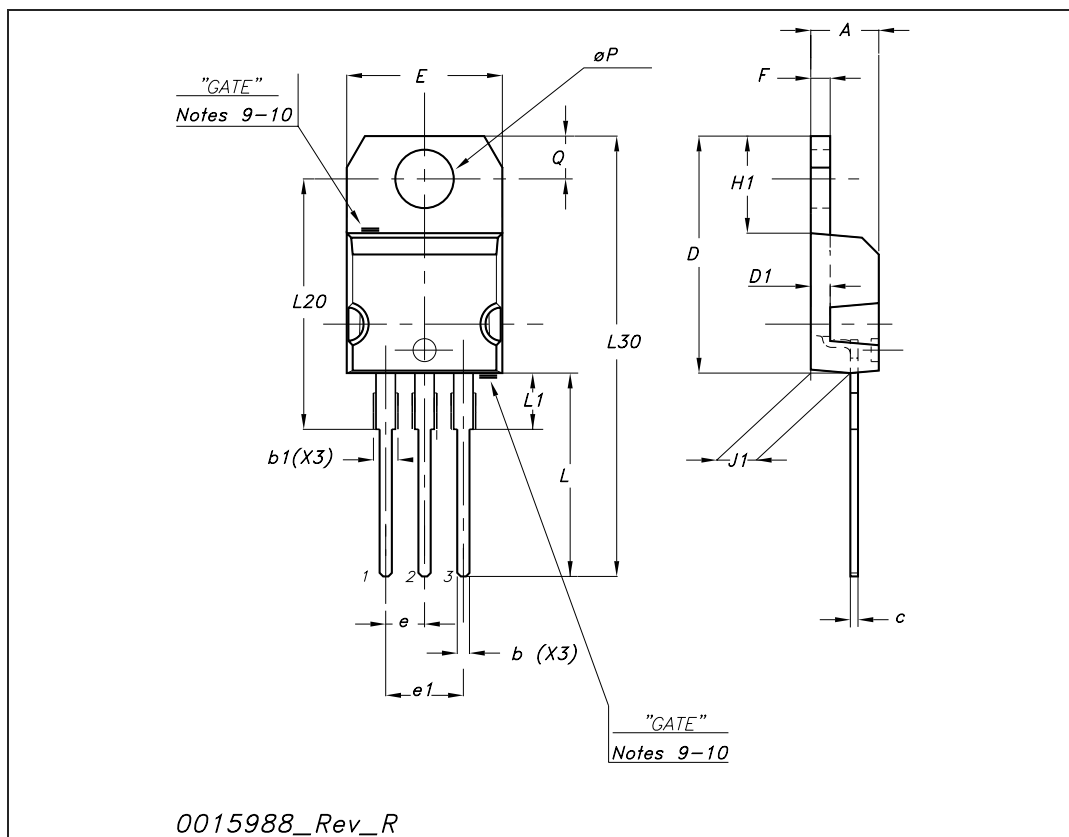


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

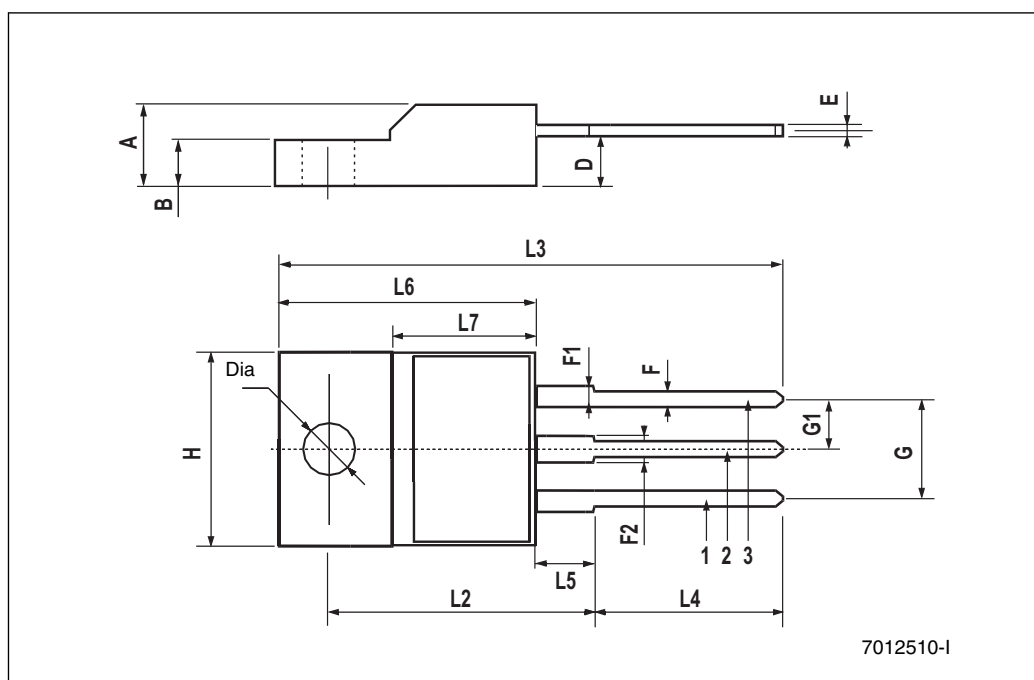
STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N Package mechanical data
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



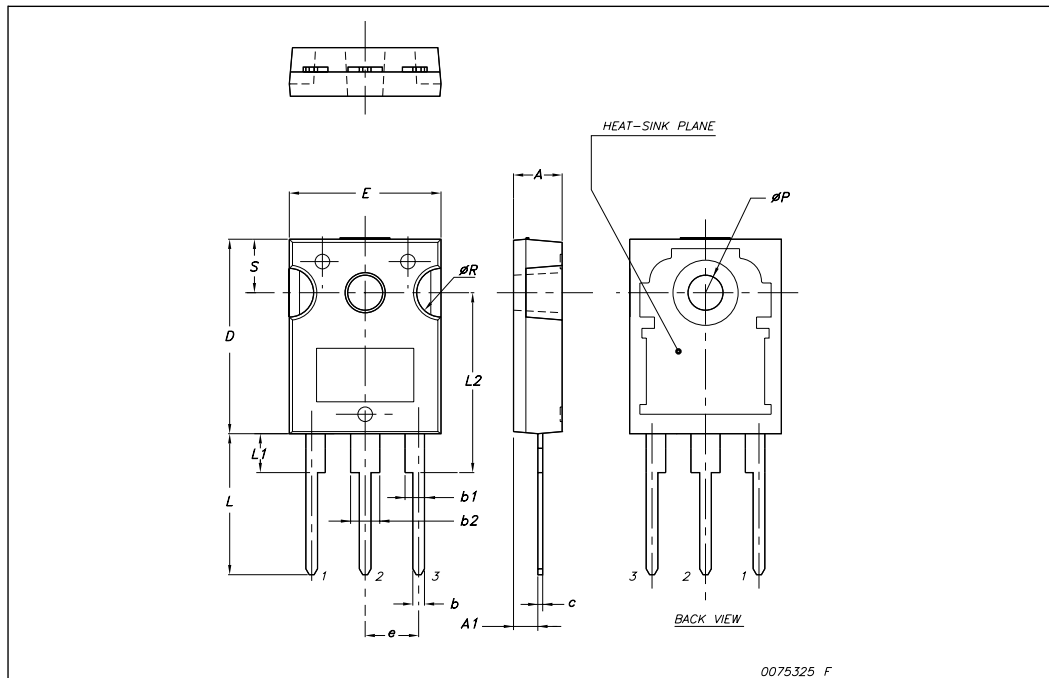
Package mechanical data STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N
TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



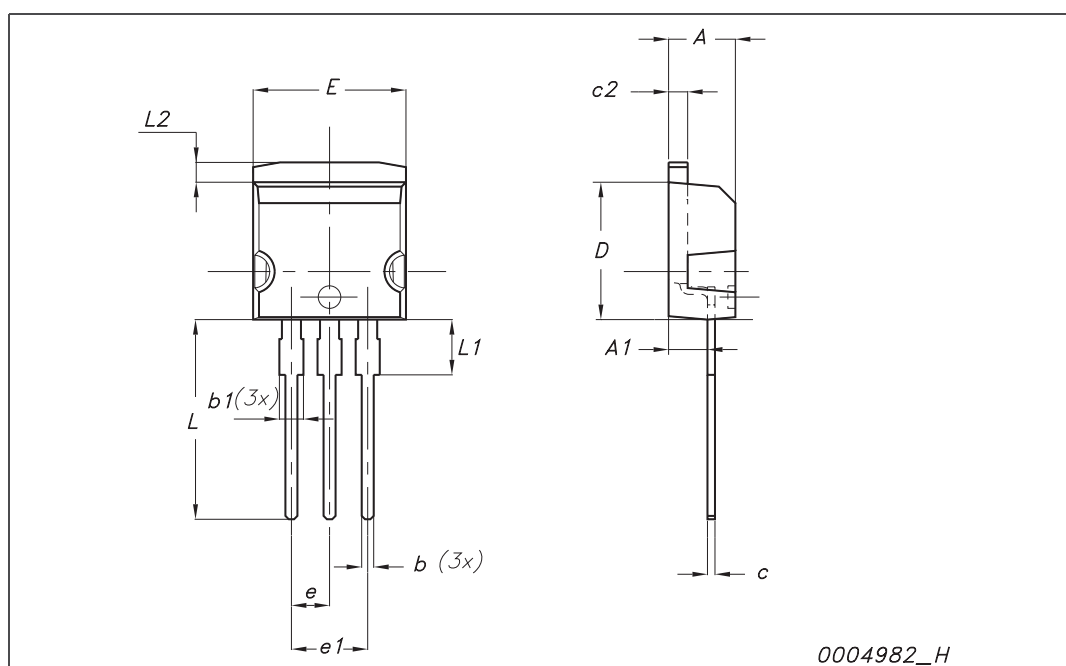
STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N Package mechanical data
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



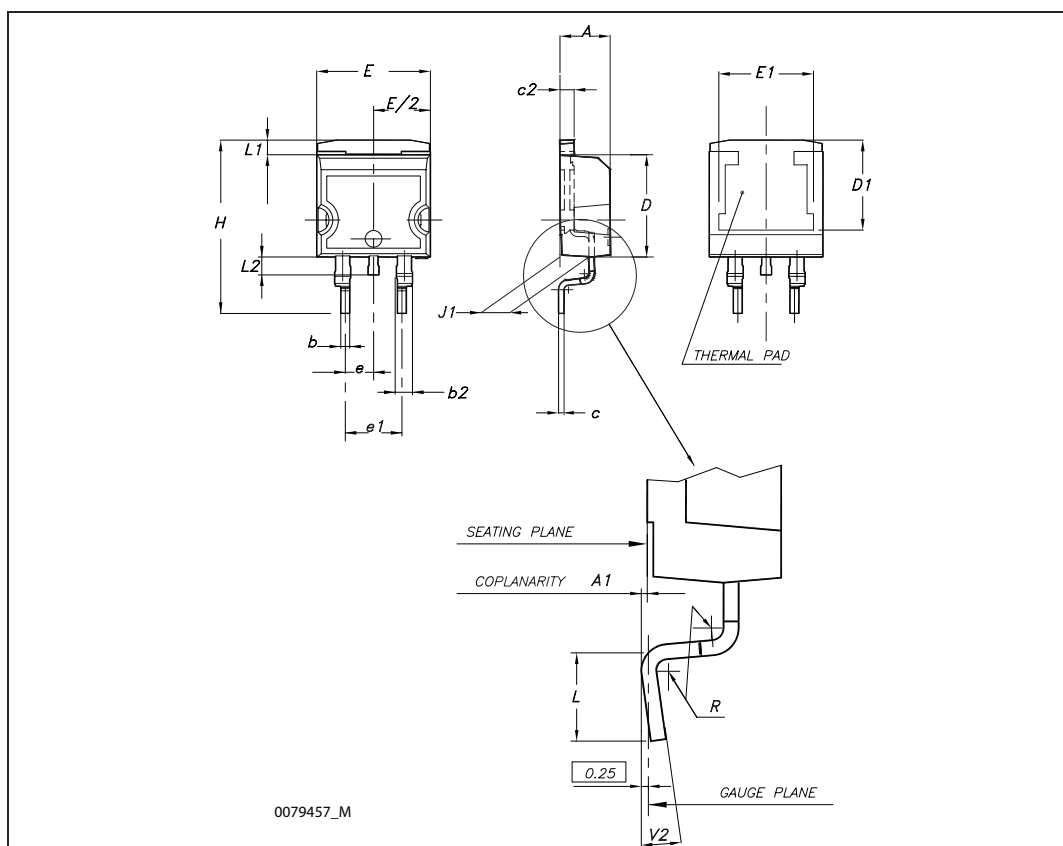
Package mechanical data STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



STB30NM60N,STI30NM60N,STF30NM60N,STP30NM60N,STW30NM60N Package mechanical data
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

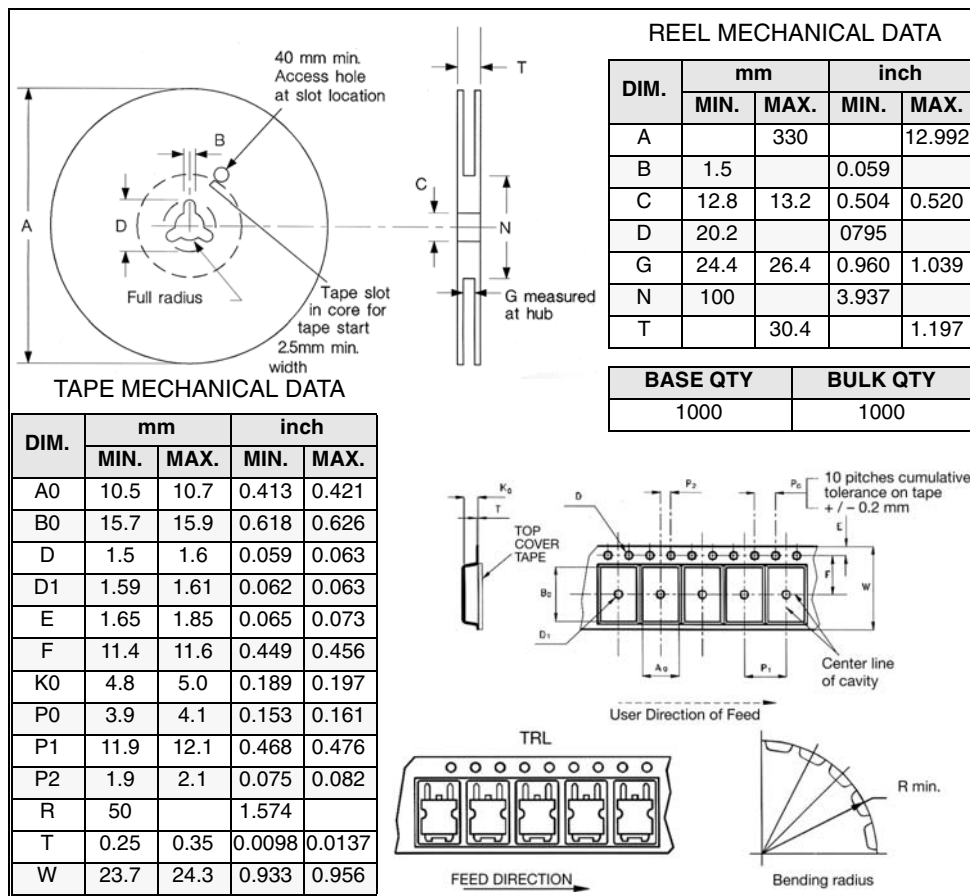


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
23-Oct-2007	1	First release.
09-Jul-2008	2	Document status promoted: from preliminary data to datasheet.

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